

S1AF THRU S1MF

ERPRISE 1.0AMP. GLASS PASSIVATED SURFACE MOUNT RECTIFIERS

PINGWEI ENTERPRISE 1.0AMP. GLASS	PASSIVA	ATED S	SURFA	CE MO	DUNT I	RECTI	FIERS					
FEATURE		SMF										
. High current capability												
. Low forward voltage drop												
. Low power loss, high efficiency												
. High temperature soldering guaranteed:		<u>.096 (2.45)</u> .108 (2.75) <u>.059 (1.5)</u>										
260° C/10 seconds at terminals.												
. For surface mounted application												
. Easy pick and place		<u></u>										
MECHANICAL DATA		.132 (3.35)										
		.006 (0.15) .144 (3.65)										
. Case: Molded plastic	.010 (0.25) .043 (0.1)											
. Epoxy: UL94V-0 rate flame retardant												
Lead: MIL-STD- 202E, Method 208 guaranteed												
. Polarity: Color band denotes cathode end	<u>.028 (0.70)</u> .047 (1.20) .028 (0.70)											
Packaging:12mm tape per EIA STD RS-481												
. Mounting position: Any Dimensions in inches and (millimeters) MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS												
Ratings at 25°C ambient temperature unless other Single phase, half wave, 60Hz, resistive or induct For capacitive load, derate current by 20%							1					
Type Number	SYMBOL	S1AF	S1BF	S1DF	S1GF	S1JF	S1KF	S1MF	units			
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V			
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V			
Maximum DC blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V			
Maximum Average Forward Rectified Current	I _{F(AV)} 1.0											
at $T_A = 55^{\circ}C$	I _{F(AV)}	1.0							A			
Peak Forward Surge Current 8.3ms single half												
sine-wave superimposed on rated load (JEDEC	<i>I</i> _{FSM} 30.0							A				
method)												
Maximum Instantaneous forward Voltage at	T/	1.0							N7			
1.0A DC	V _F								V			
Maximum DC Reverse Current $@T_A = 25^{\circ}C$	-	5.0							μΑ			
at rated DC blocking voltage $@T_A = 125^{\circ}C$	<i>I</i> _R 100.0											
Typical Junction Capacitance (Note1)	Сл	15							pF			
Typical Thermal Resistance (Note 2)	R _(JA)	75							°C /W			
Storage Temperature	T _{STG}	-55 to +150							°C			
Operation Junction Temperature	TJ	-55 to +150							°C			
-	1	1							1			

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc

2. Measured on P.C. Board with 0.2×0.2"(5.0×5.0mm)Copper Pad Areas.